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SUBMISSION TYPE: Information Disclosure Statement

APPLICATION NUMBER: 09687048

FIRST NAMED INVENTOR: Kuri-shi Lee

TITLE OF INVENTION: LEADFRAME AND SEMICONDUCTOR PACKAGE WITH IMPROVED

SOLDER JOINT STRENGTH

ATTORNEY DOCKET NUMBER: AMKOR-052A

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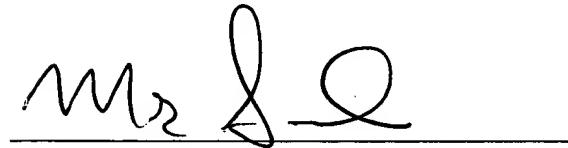
Title: LEADFRAME AND SEMICONDUCTOR PACKAGE WITH
IMPROVED SOLDER JOINT STRENGTH

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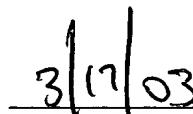
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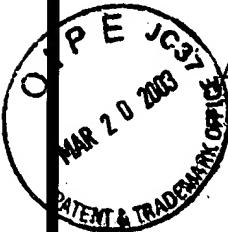


Mark B. Garred



Date

34,823
Registration No.



ATTORNEY DOCKET NO: AMKOR-052A

TITLE: Leadframe and semiconductor package with improved solder joint strength

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TRANSMITTAL FORM

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Total Number of Pages in This Submission

Application Number
09/687,048

Filing Date
10/13/2000

First Named Inventor
Tae Heon Lee

Group Art Unit
2814

Examiner Name
Nguyen, Dilinh P.

Attorney Docket Number
AMKOR-052A

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Firm or Individual name	Mark B. Garred STETINA BRUNDA GARRED & BRUCKER	
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Date	3/17/03	

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Submission Type: Information
Disclosure Statement

Application Number: 09/687,048

Attorney Docket Number: AMKOR-052A

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LEADFRAME AND SEMICONDUCTOR PACKAGE WITH IMPROVED SOLDER JOINT STRENGTH

First Named Inventor: Kuri-shi Tae Heon Lee

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Name: Mark B. Garred
Registration Number: 34,823
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Stylesheet Version: 1.0

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ADDITIONAL FEES

Fee Description	Number	Quantity	Fee Code	Amount	Fee Paid
Submission Of Information Disclosure Stmt Fee		1	1806	\$ 180	\$ 180

Subtotal For Additional Fees: \$ 180

MANUFACTURE OF SEMICONDUCTOR DEVICE

Patent Number: JP10256240
Publication date: 1998-09-25
Inventor(s): FUKAZAWA MASANAGA;; KADOMURA SHINGO;; FUKUDA
Applicant(s): SONY CORP
Requested Patent: JP10256240
Application: JP19970158570 19970616
Priority Number(s):
IPC Classification: H01L21/3065; H01L21/768
EC Classification:
Equivalents:

Abstract

PROBLEM TO BE SOLVED: To form a connection hole in an interlayer insulating film by a dry etching process, using not only a general composition etching gas but also an etching gas containing no fluorocarbon-loosed gas.

SOLUTION: This method for manufacturing a semiconductor device includes a step of forming a connection hole 14 in an inter-layer insulating film by a dry etching process using an etching gas. In this case, a film 12 having a low dielectric constant is an insulating film which is made of a compound, having SiF or CF couplings in a chemical structural formula. Specifically, the compound may be SiOF, cyclic fluororesin siloxane copolymer or polyfluoroaryl ether. When such an insulating film employed, active species of F- or fluoroacarbon- boased molecules emitted from inside of the connection hole 24 of the inter-layer insulating film can cause an etching rate of the insulating film inside the hole 14 to be increased.

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CLAIMS

[Claim(s)]

[Claim 1] the layer insulation film which consists of a compound which has SiF combination or CF combination in a chemical structure formula by the dry etching using etching gas -- connection -- the manufacture method of the semiconductor device characterized by having the process which forms a hole

[Claim 2] The compound which has SiF combination or CF combination in a chemical structure formula is the manufacture method of the semiconductor device according to claim 1 characterized by the ranges of specific inductive capacity being 1-4.

[Claim 3] the compound which has SiF combination or CF combination in a chemical structure formula -- under etching -- connection of a layer insulation film -- a hole -- the active species of the molecule of F emitted from inside, or a fluorocarbon system -- connection -- a hole -- the manufacture method of the semiconductor device according to claim 1 characterized by including F beyond the grade which can be made to accelerate etching of an inner insulator layer

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DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[Drawing 1] the connection formed in the layer insulation film according to the example of this invention -- it is the outline cross section showing a hole

[Drawing 2] It is the outline cross section showing the structure of the sample used for the example of this invention.

[Drawing 3] the connection which tried to form in the layer insulation film used for comparison with the example of this invention -- it is the outline cross section showing a hole

[Description of Notations]

10 Si Substrate and 11 SiO₂ Layer and 12 Low Dielectric Constant Film and 13 Photoresist and 14 Connection -- Hole

[Translation done.]